

INSTITUTE OF AERONAUTICAL ENGINEERING

(Autonomous)

Dundigal, Hyderabad -500 043

INFORMATION TECHNOLOGY

COURSE DESCRIPTOR

Course Title	SEMIC	SEMICONDUCTOR PHYSICS									
Course Code	AHSB	AHSB13									
Programme	B.Tech	3.Tech									
Semester	ΙΙ	II CSE IT									
Course Type	Founda	Foundation									
Regulation	IARE -	IARE - R18									
	Theory Practical										
Course Structure	Lectu	res	Tutorials	Credits	Laboratory	Credits					
	3		1	4	3	1.5					
Chief Coordinator	Ms. S G	Charv	vani, Assistant Pro	ofessor							
Course Faculty		Dr. P Koteshwar Rao, Professor Dr. Y Veeraswamy, Professor Mr. K Sai Baba, Assistant Professor									

I. COURSE OVERVIEW:

The course matter is divided into five modules covering duly-recognized areas of theory and study. This course develops abstract and critical reasoning by studying mathematical and logical proofs and assumptions as applied in basic physics. The topics include quantum mechanics, semiconductors, opto electronic devices, magnetism, dielectrics, lasers and fiber optics. The course helps students to gain knowledge of basic principles and appreciate the diverse real-time applications in technological fields in respective branches.

II. COURSE PRE-REQUISITES:

Level	Course Code	Semester	Prerequisites					
-	-	-	Basic principles of semiconductors					

III. MARKS DISTRIBUTION:

Subject	SEE Examination	CIA Examination	Total Marks	
Semiconductor Physics	70 Marks	30 Marks	100	

~	Chalk & Talk	~	Quiz	✔ Assignments		×	MOOCs
~	LCD / PPT	~	Seminars	×	Mini Project	~	Videos
×	Open Ended Experiment	S					

IV. DELIVERY / INSTRUCTIONAL METHODOLOGIES:

V. EVALUATION METHODOLOGY:

The course will be evaluated for a total of 100 marks, with 30 marks for Continuous Internal Assessment (CIA) and 70 marks for Semester End Examination (SEE). Out of 30 marks allotted for CIA during the semester, marks are awarded by taking average of two CIA examinations or the marks scored in the make-up examination.

Semester End Examination (SEE): The SEE is conducted for 70 marks of 3 hours duration. The syllabus for the theory courses is divided into FIVE modules and each module carries equal weightage in terms of marks distribution. The question paper pattern is as follows. Two full questions with "either" or "choice" will be drawn from each module. Each question carries 14 marks. There could be a maximum of two sub divisions in a question.

The emphasis on the questions is broadly based on the following criteria:

50 %	To test the objectiveness of the concept.
50 %	To test the analytical skill of the concept OR to test the application skill of the concept.

Continuous Internal Assessment (CIA):

CIA is conducted for a total of 30 marks (Table 1), with 20 marks for Continuous Internal Examination (CIE), 05 marks for Quiz and 05 marks for Alternative Assessment Tool (AAT).

Component		Theory	Total Marka		
Type of Assessment	CIE Exam	Quiz	AAT	Total Marks	
CIA Marks	20	05	05	30	

Continuous Internal Examination (CIE):

Two CIE exams shall be conducted at the end of the 8th and 16th week of the semester respectively. The CIE exam is conducted for 20 marks of 2 hours duration consisting of five descriptive type questions out of which four questions have to be answered where, each question carries 5 marks. Marks are awarded by taking average of marks scored in two CIE exams.

Quiz - Online Examination

Two Quiz exams shall be online examination consisting of 25 multiple choice questions and are to be answered by choosing the correct answer from a given set of choices (commonly four). Such a question paper shall be useful in testing of knowledge, skills, application, analysis, evaluation and understanding of the students. Marks shall be awarded considering the average of two quiz examinations for every course.

Alternative Assessment Tool (AAT)

This AAT enables faculty to design own assessment patterns during the CIA. The AAT converts the classroom into an effective learning centre. The AAT may include tutorial hours/classes,

seminars, assignments, term paper, open ended experiments, METE (Modeling and Experimental Tools in Engineering), five minutes video, MOOCs etc.

The AAT chosen for this course is given in section XI.

VI. HOW PROGRAM OUTCOMES ARE ASSESSED:

	Program Outcomes (POs)	Strength	Proficiency assessed by
PO 1	Engineering knowledge: Apply the knowledge of	3	Presentation on
	mathematics, science, engineering fundamentals, and an engineering specialization to the solution of complex		real-world problems
	engineering specialization to the solution of complex engineering problems.		
PO 2	Problem analysis: Identify, formulate, review research	2	Term paper
	literature, and analyze complex engineering problems reaching		
	substantiated conclusions using first principles of mathematics,		
	natural sciences, and engineering sciences		
PO 4	Conduct investigations of complex problems: Use research-	1	Seminars
	based knowledge and research methods including design of		
	experiments, analysis and interpretation of data, and synthesis		
	of the information to provide valid conclusions.		

3 = High; **2** = Medium; **1** = Low

VII. HOW PROGRAM SPECIFIC OUTCOMES ARE ASSESSED:

	Program Specific Outcomes (PSOs)	Strength	Proficiency assessed by
PSO 1	Professional Skills: The ability to understand, analyze and develop computer programs in the areas related to algorithms, system software, multimedia, web design, big data analytics, and networking for efficient analysis and design of computer - based systems of varying complexity.	1	Seminar
PSO 2	Software Engineering Practices: The ability to apply standard practices and strategies in software service management using open-ended programming environments with agility to deliver a quality service for business success.	-	-
PSO 3		-	-

3 = High; **2** = Medium; **1** = Low

VIII. COURSE OBJECTIVES (COs):

The course s	The course should enable the students to:								
I Enrich knowledge in principles of quantum mechanics and semiconductors.									
II	Develop strong fundamentals of electronic and optoelectronic materials.								
III	Enrich knowledge about measuring resistivity, conductivity and other parameters.								
IV	Correlate principles and applications of lasers and fiber optics.								

IX. COURSE LEARNING OUTCOMES (CLOs):

CLO	CLO's	At the end of the course, the student will	PO's	Strength of Mapping
Code		have the ability to:	Mapped	
AHSB13.01	CLO 1	Recall the basic principles of physics and	PO 1,	3
		apply these concepts of physics in solving the	PO 2	
		real-time problems.		
AHSB13.01	CLO 2	Acquire knowledge about fundamentals in	PO 1	3
		quantum mechanics.		
AHSB13.01	CLO 3	Interpretation of dual nature of matter wave	PO 1	3
		concept using Davisson & Germer's		
		experiment.		
AHSB13.01	CLO 4	Estimate the energy of the particles using	PO 1	3
		Schrödinger's wave equation and apply it to		
		particle in potential box.		
AHSB13.01	CLO 5	Understand the band structure of a solid and	PO 1	3
		Classify materials as metals, insulators,		
		or semiconductors, and sketch a schematic		
		band diagram for each one.		
AHSB13.01	CLO 6	Recollect the conductivity mechanism	PO 1	3
		involved in semiconductors and calculate		
		carrier concentrations.		
AHSB13.01	CLO 7	Acquire knowledge about fundamentals in	PO 1	3
		semiconducting devices		
AHSB13.01	CLO 8	Understand the basics of a p-n junction and	PO 1,	3
		construction of optoelectronic devices like	PO 2	
		LED, photo diode, solar cell.		
AHSB13.01	CLO 9	Recollect the concept of electric polarization	PO 1	2
		and classify dielectric materials.		
AHSB13.01	CLO 10	Recollect the concept of magnetization and	PO 1	3
		classify magnetic materials.		
AHSB13.01	CLO 11	Apply different laws of radiation to	PO 1	3
		understand the phenomenon behind		
		production of light.		
AHSB13.01	CLO 12	Understand the basic principles involved in	PO 2,	2
		the production of Laser light and also Real-	PO 5	
		time applications of lasers.		
AHSB13.01	CLO 13	Recollect basic principle, construction, types	PO 1	3
		and attenuation of optical fibers.		
AHSB13.01	CLO 14	Understand the importance of optical fibers	PO 5	2
		in real-time communication system.		

3 = High; 2 = Medium; 1 = Low

X. MAPPING COURSE LEARNING OUTCOMES LEADING TO THE ACHIEVEMENT OF PROGRAM OUTCOMES AND PROGRAM SPECIFIC OUTCOMES:

Course Learning		Program Outcomes (POs)								Program Specific Outcomes (PSOs)					
Outcomes (CLOs)	PO1	PO2	PO3	PO4	PO5	PO6	PO7	PO8	PO9	PO10	PO11	PO12	PSO1	PSO2	PSO3
CLO 1	3	2											1		
CLO 2	3														
CLO 3	3														
CLO 4	3														

CLO 5	3								
CLO 6	3								
CLO 7	3								
CLO 8	3	2							
CLO 9		2							
CLO 10	3								
CLO 11	3								
CLO 12		2		1				1	
CLO 13	3								
CLO 14				1				1	

3 = High; 2 = Medium; 1 = Low

XI. ASSESSMENT METHODOLOGIES – DIRECT

CIE Exams	PO 1	SEE Exams	PO 1	Assignments	-	Seminars	PO 5
Laboratory Practices	-	Student Viva	-	Mini Project	-	Certification	-
Term Paper	PO 1						

XII. ASSESSMENT METHODOLOGIES - INDIRECT

~	Early Semester Feedback	~	End Semester OBE Feedback
×	Assessment of Mini Projects by Experts		

XIII. SYLLABUS

Module-I	QUANTUM MECHANICS					
Introduction to quantum physics, Black body radiation, Planck's law, Photoelectric effect, Compton effect, De-Broglie's hypothesis, Wave-particle duality, Davisson and Germer experiment, Time-independent Schrodinger equation for wave function, Born interpretation of the wave function, Schrodinger equation for one dimensional problems–particle in a box.						
Module-II	ELECTRONIC MATERIALS AND SEMICONDUCTORS					
treatment), Or Intrinsic and	Free electron theory, Bloch's theorem for particles in a periodic potential, Kronig-Penney model (Qualitative treatment), Origin of energy bands, Types of electronic materials: metals, semiconductors, and insulators. Intrinsic and extrinsic semiconductors, Carrier concentration, Dependence of Fermi level on carrier-concentration and temperature, Hall effect.					
Module-III	LIGHT-SEMICONDUCTOR INTERACTION					
Carrier generation and recombination, Carrier transport: diffusion and drift, Direct and indirect band gaps, p-n junction, V-I characteristics, Energy Band diagram, Biasing of a junction.						
Photo voltaic cell.	Photo voltaic effect, Construction and working of LED, Photo detectors, PIN, Avalanche photodiode, Solar cell.					

Module-IV ENGINEERED ELECTRIC AND MAGNETIC MATERIALS					
Polarization, Permittivity, Dielectric constant, Internal field in solids, Clausius Mosotti equation,					
Ferroelectricity, Piezoelectricity, Pyroelectricity.					
Magnetization, Permeability, Susceptibility, Classification of dia, Para and Ferro magnetic materials on the					
basis of magnetic moment, Domain theory of Ferro magnetism on the basis of hysteresis curve.					
Module-V LASERS AND FIBER OPTICS					
Characteristics of lasers, Spontaneous and stimulated emission of radiation, Metastable state, Population					
inversion, Lasing action, Ruby laser, Semiconductor diode laser and applications of lasers.					
Principle and construction of an optical fiber, Acceptance angle, Numerical aperture, Types of optical fibers					
(Single mode, multimode, step index, graded index), Attenuation in optical fibers, Optical fiber communication					
system with block diagram.					
Text Books:					
1. Dr. K. Vijaya Kumar, Dr. S. Chandralingam, "Modern Engineering Physics", Chand & Co. New Delhi, 1st Edition, 2010.					
2. Dr. M. N. Avadhanulu, Dr. P. G. Kshirsagar, A text book of engineering physics, S. Chand.					
3. B. K Pandey and S. Chaturvedi, Engineering physics – Cengage learning					
Reference Books:					
1. J. Singh, Semiconductor Optoelectronics: Physics and Technology, McGraw-Hill Inc. (1995).					
2. R. K. Gaur, S. L. Gupta, "Engineering Physics", Dhanpat Rai Publications, 8th Edition, 2001					
3. Online course: "Optoelectronic Materials and Devices" by Monica Katiyar and Deepak Gupta					

on NPTEL.

4. O. Svelto, "Principles of Lasers", Springer Science & Business Media, 2010

XIV. COURSE PLAN:

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The course plan is meant as a guideline. Probably there may be changes.

Lecture No	Topics to be covered	Course Learning Outcomes (CLOs)	Reference
1	Introduction to quantum physics	CLO 2	T2:5.5 R1:1.12.1
2	Black body radiation	CLO 2	T2:5.6 R1:1.12.3
3	Planck's law, Photoelectric effect, Compton effect	CLO 2	T2:5.10 R1:1.15
4	De-Broglie's hypothesis, Wave-particle duality	CLO 3	T2:5.15 R1:1.16
5	Davisson and Germer experiment	CLO 3	T2:5.17 R1:1.13.1
6	Time-independent Schrodinger equation for wave function	CLO 4	T2:5.18 R1:1.13.2
7	Born interpretation of the wave function	CLO 4	T2:5.19 R1:1.13.3
8	Schrodinger equation for one dimensional problems-particle in a box.	CLO 4	T2:5.20 R1:1.17.1
9	Bloch's theorem for particles in a periodic potential, Kronig-Penney model (Qualitative treatment)	CLO 5	T2:5.24 R1:1.17.3
10	Kronig-Penney model (Qualitative treatment)	CLO 5	T2:6.1 R1:2.3
11	Origin of energy bands	CLO 5	T2:6.3 R1:2.6.1
12	Types of electronic materials: metals, semiconductors, and insulators	CLO 5	T2:6.5 R1:2.6.2
13	Intrinsic semiconductors Carrier concentration	CLO 6	T2:7.3 R1:2.8

Lecture No	Topics to be covered	Course Learning Outcomes (CLOs)	Reference
14	Intrinsic semiconductors Carrier concentration	CLO 6	T2:7.5,7.6 R1:2.9.2
15	Extrinsic semiconductors, Carrier concentration	CLO 6	T2:7.7 R1:2.10
16	Extrinsic semiconductors, Carrier concentration	CLO 6	T2:7.7 R2:2.10
17	Dependence of Fermi level on carrier-concentration and temperature	CLO 6	T2:7.11 R2:2.10.2
18	Carrier generation and recombination, Hall effect	CLO 6	T2:7.11 R2:2.32
19	Carrier generation and recombination, Carrier transport: diffusion and drift, Direct and indirect band gaps	CLO 7	T2:7.11 R2:2.10
20	p-n junction, V-I characteristics	CLO 7	T2:7.12 R2:2.10.3
21	Energy Band diagram, Biasing of a junction	CLO 8	T2:7.12 R2:2.10.3
22	Photo voltaic effect, Construction and working of LED	CLO 8	T2:7.13 R1:2.10.4
23	Photo detectors, PIN, Avalanche photodiode	CLO 8	T2:7.14 R1:2.10.6
24	Solar cell	CLO 8	T2:7.15 R1:2.10.7
25	Polarization, Permittivity, Dielectric constant	CLO 9	T1:7.15 R2:2.10.7
26	Internal field in solids, Clausius Mosotti equation	CLO 9	T1:7.15 R2:2.10.7
27	Ferro electricity	CLO 9	T1:7.15 R2:2.10.7
28	Piezoelectricity, Pyroelectricity	CLO 9	T1:7.15 R2:2.10.7
29	Magnetization, Permeability, Susceptibility	CLO 10	T1:16.9 R2:8.11.1
30	Classification of dia, para and ferro magnetic materials on the basis of magnetic moment	CLO 10	T1:16.9 R2:8.11.2
31	Domain theory of Ferro magnetism on the basis of hysteresis curve	CLO 10	T1:16.8 R2:8.12.1
32	Introduction and Characteristics of lasers	CLO 11	T1:15.2 R4:8.2
33	Spontaneous and stimulated emission of radiation	CLO 11	T2:15.7 R4:8.3.3
34	Metastable state, Population inversion, Lasing action	CLO 11	T2:15.13 R4:8.7.2
35	Ruby laser	CLO 12	T2:15.13 R4:8.7.2
39	He-Ne laser and applications of lasers	CLO 12	T2:15.16 R1:8.7.3
40	Introduction and Principle and construction of an optical fiber	CLO 13	T1:11.9
41	Acceptance angle, Numerical aperture	CLO 13	R2:12.24 T1:11.9
42	Types of optical fibers (Single mode, multimode, step index, graded	CLO 13	R3:12.25 T1:3.2
43	index) Attenuation in optical fibers	CLO 13	R3:3.2 T1:3.3.1
44	Optical fiber communication system with block diagram.	CLO 14	R3:3.2 T2:16.5 R3:8.10

XV. GAPS IN THE SYLLABUS - TO MEET INDUSTRY / PROFESSION REQUIREMENTS:

S NO	DESCRIPTION	PROPOSED ACTIONS	RELEVANCE WITH POs	RELEVANCE WITH PSOs
1	Encourage the students to design the	Seminars /	PO 2	PSO 1
	working models which are correlated	Laboratory		
	with the syllabus.	Practices		
2	Insist the students to collect real- time	Seminars /	PO 1	PSO 1
	applications of the basic principles	NPTEL		
	they learn in physics.			
3	Motivate the students to organize the	Seminars /	PO 5	PSO 1
	seminars for the awareness of	NPTEL		
	upcoming applications in physics.			

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